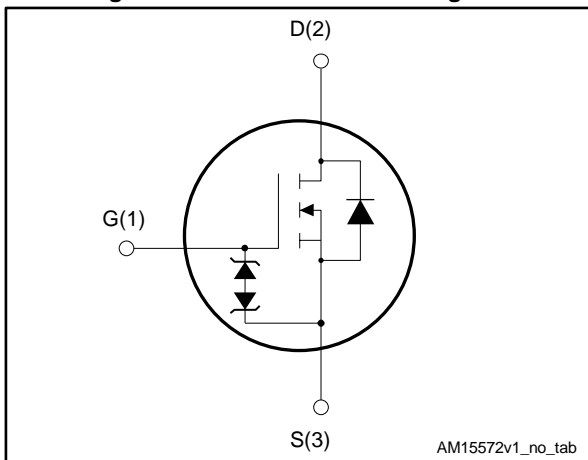


N-channel 650 V, 1.5 Ω typ., 4.5 A SuperMESH™ Power MOSFET in a TO-220FP package

Datasheet - preliminary data



Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STF5NK65Z	650 V	1.8 Ω	4.5 A	25 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Zener-protected

Applications

- Switching applications

Description

This high voltage device is a Zener-protected N-channel Power MOSFET developed using the SuperMESH™ technology by STMicroelectronics, an optimization of the well-established PowerMESH™. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Table 1: Device summary

Order code	Marking	Package	Packaging
STF5NK65Z	5NK65Z	TO-220FP	Tube

Contents

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage	650	V
V _{GS}	Gate-source voltage	±30	V
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25 °C	4.5	A
I _D ⁽¹⁾	Drain current (continuous) at T _C = 100 °C	3.1	A
I _{DM} ⁽¹⁾⁽²⁾	Drain current (pulsed)	18	A
P _{TOT}	Total dissipation at T _C = 25 °C	25	W
ESD	Gate-source, human body model, R = 1.5 kΩ, C = 100 pF	2	kV
dv/dt ⁽³⁾	Peak diode recovery voltage slope	4.5	V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)	2.5	kV
T _{stg}	Storage temperature range	-55 to 150	°C
T _j	Operation junction temperature range		

Notes:

(1)Limited by maximum junction temperature

(2)Pulse width limited by safe operating area

(3) $I_{SD} \leq 4.5$ A, $di/dt \leq 200$ A/ μ s, $V_{DD} = 80\%$ V_{(BR)DSS}.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case	5	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	62.5	°C/W

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _{j,Max})	4.2	A
E _{AS}	Single pulse avalanche energy (starting T _J =25 °C, I _D =I _{AR} , V _{DD} =50 V)	170	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}^{(1)}$			50	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.1\text{ A}$		1.5	1.8	Ω

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	-	680	-	pF
C_{oss}	Output capacitance		-	80	-	pF
C_{riss}	Reverse transfer capacitance		-	17	-	pF
$C_{oss\ eq}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ to }520\text{ V}$	-	98	-	pF
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 4.5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 15: "Test circuit for gate charge behavior")	-	25	-	nC
Q_{gs}	Gate-source charge		-	4.4	-	nC
Q_{gd}	Gate-drain charge		-	13.7	-	nC

Notes:

⁽¹⁾ $C_{oss\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80%

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 5\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14: "Test circuit for resistive load switching times" and Figure 19: "Switching time waveform")	-	20	-	ns
t_r	Rise time		-	15	-	ns
$t_{d(off)}$	Turn-off delay time		-	140	-	ns
t_f	Fall time		-	40	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		4.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		18	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 10\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	375		ns
Q_{rr}	Reverse recovery charge		-	1.76		μC
I_{RRM}	Reverse recovery current		-	10		A

Notes:

⁽¹⁾Pulsed: pulse duration=300 μs , duty cycle 1.5%.

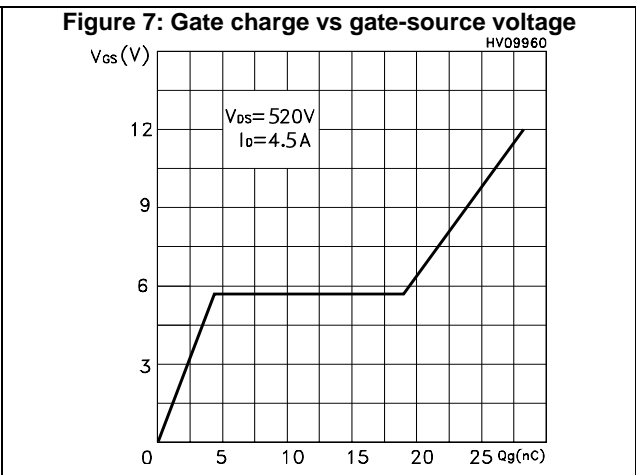
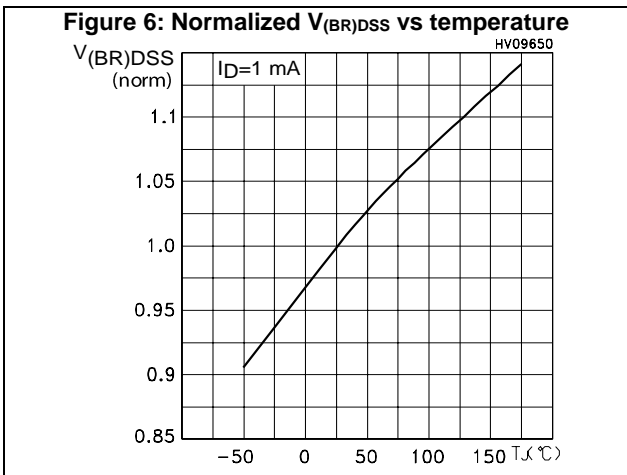
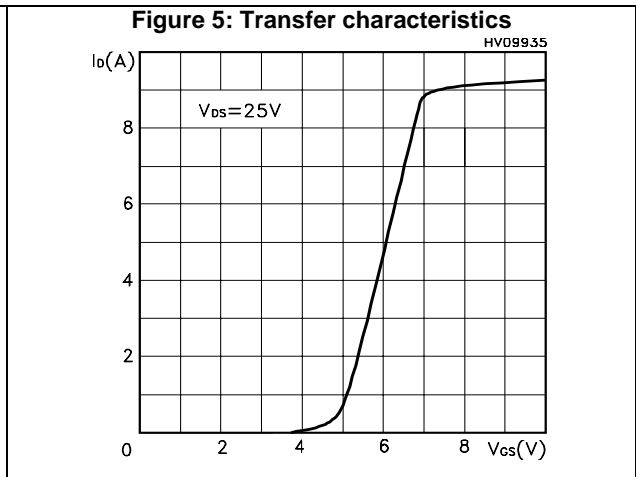
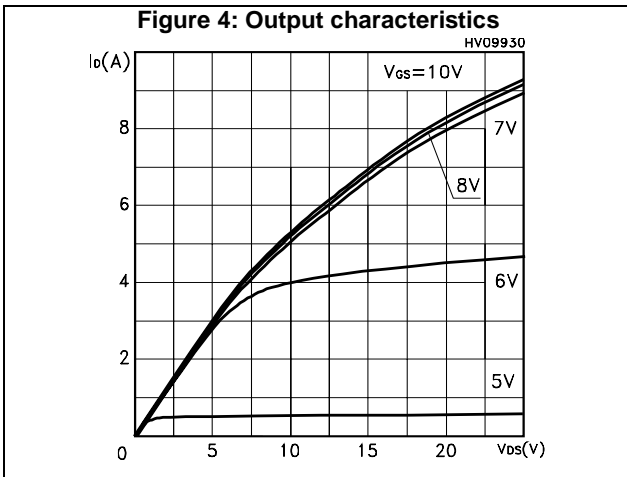
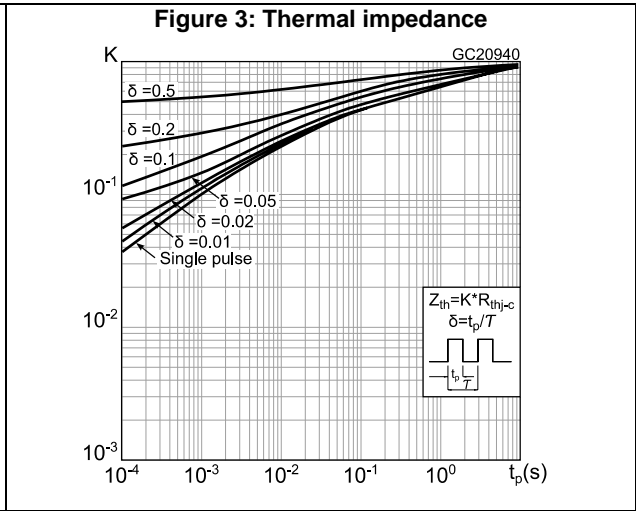
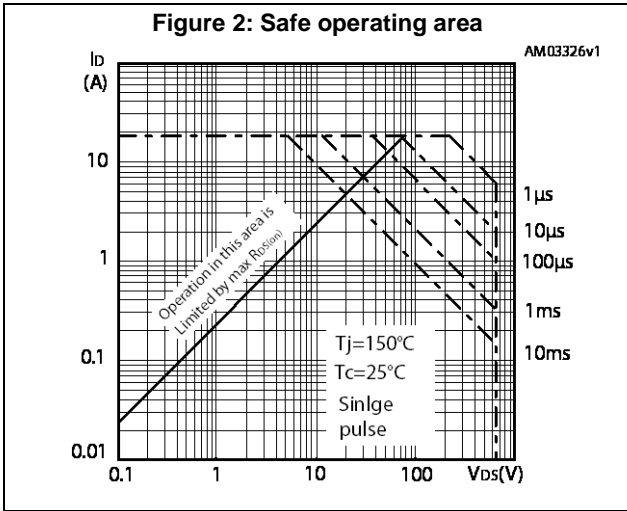
⁽²⁾Pulse width limited by safe operating area.

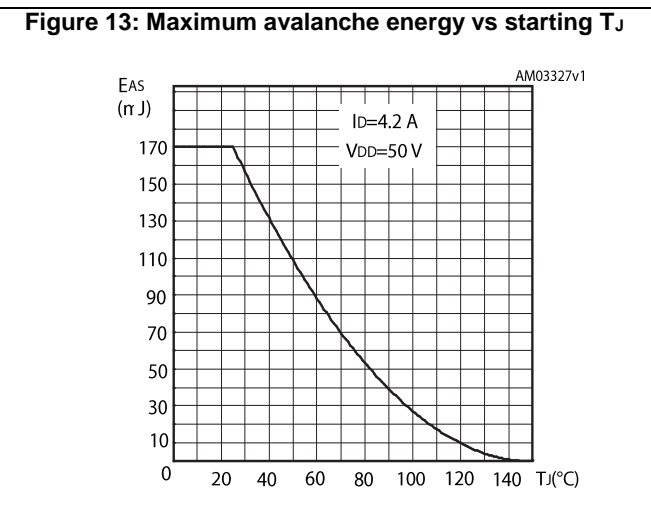
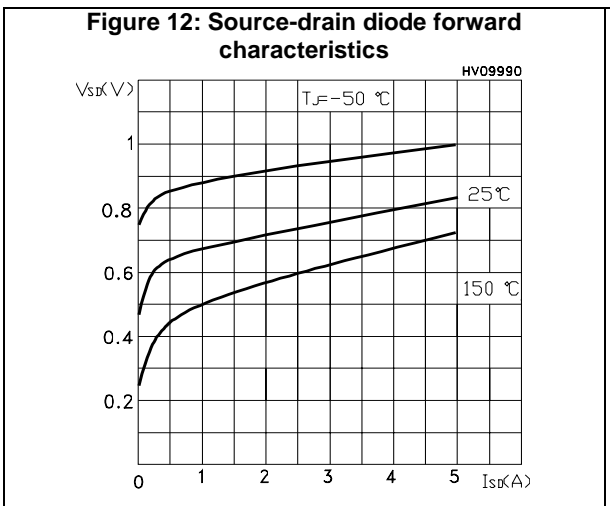
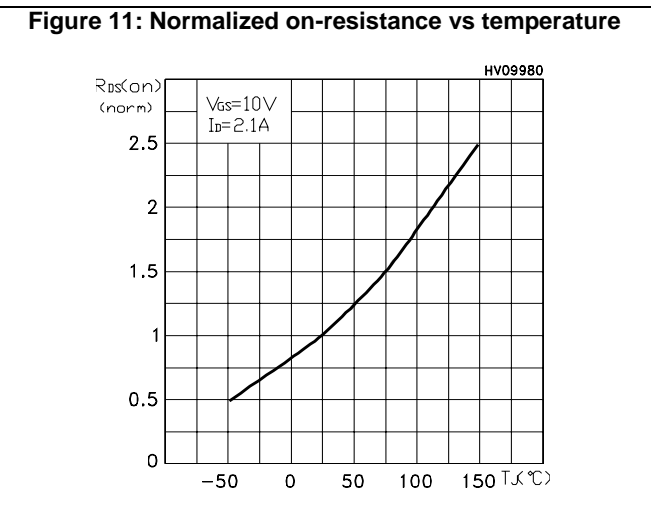
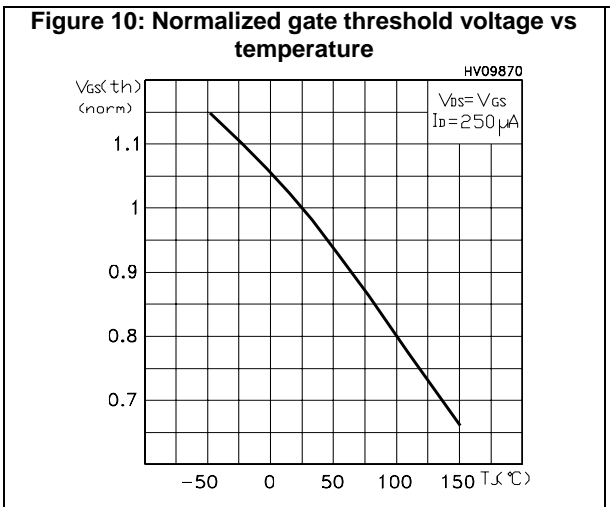
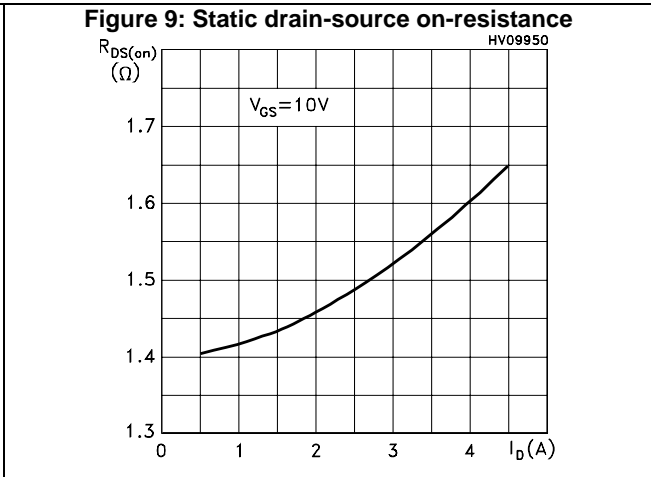
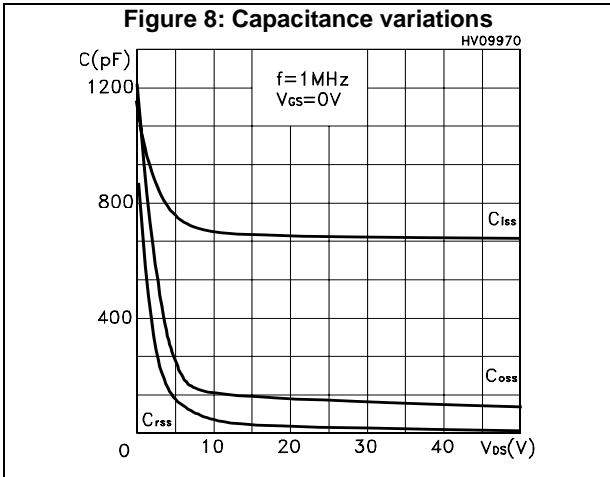
Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0\text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.2 Electrical characteristics (curves)





3 Test circuits

Figure 14: Test circuit for resistive load switching times



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Figure 15: Test circuit for gate charge behavior



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Figure 16: Test circuit for inductive load switching and diode recovery times



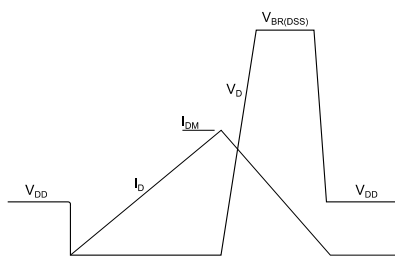
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Figure 17: Unclamped inductive load test circuit



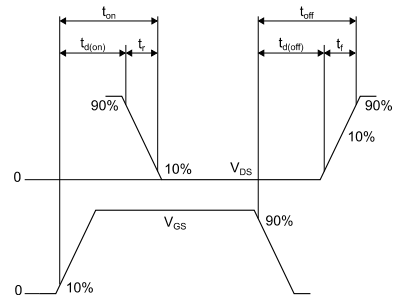
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Figure 18: Unclamped inductive waveform



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Figure 19: Switching time waveform



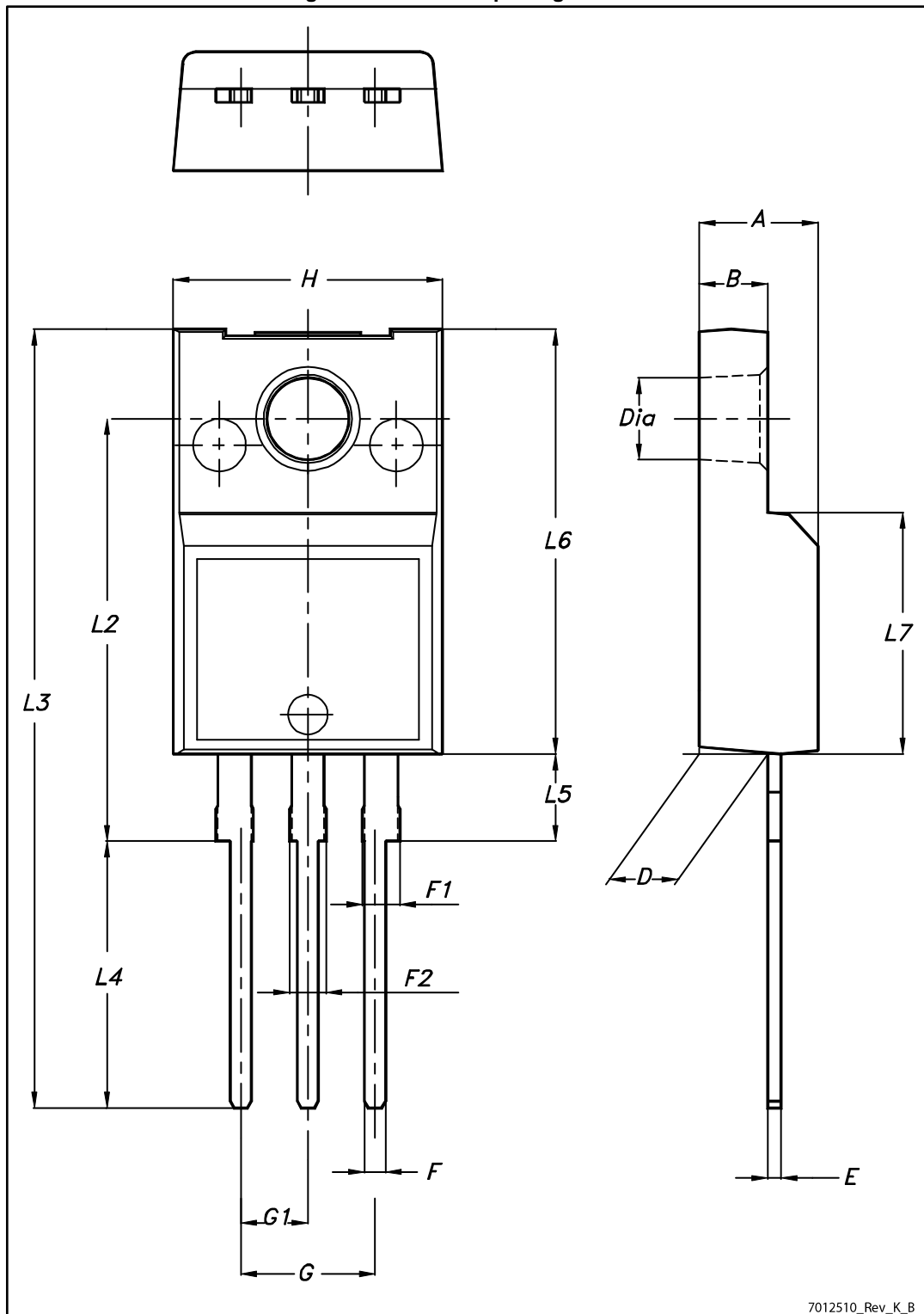
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-220FP package information

Figure 20: TO-220FP package outline



7012510_Rev_K_B

Table 10: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
11-Nov-2016	1	Initial release.

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